

P-Channel 30-V (D-S) MOSFET

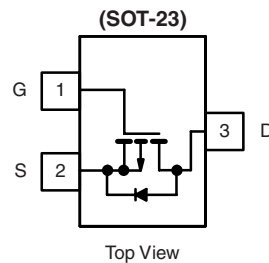
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 30	0.053 at $V_{GS} = - 10$ V	- 4.0
	0.086 at $V_{GS} = - 4.5$ V	- 3.1

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET

APPLICATIONS

- Load Switch
- PA Switch



Ordering Information: SL2343

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	$T_A = 25$ °C	- 4.0	- 3.1	A
		$T_A = 70$ °C	- 3.2	- 2.5	
Pulsed Drain Current	I_{DM}	- 15			
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	- 1.0	- 0.6		
Maximum Power Dissipation ^{a, b}	P_D	$T_A = 25$ °C	1.25	0.75	W
		$T_A = 70$ °C	0.8	0.48	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	75	100	°C/W
	Steady State		120	166	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	- 15			A
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4.0\text{ A}$		0.043	0.053	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}$		0.068	0.086	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -4.0\text{ A}$		10		S
Diode Forward Voltage	V_{SD}	$I_S = -1.0\text{ A}, V_{GS} = 0\text{ V}$		- 0.7	- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}$ $I_D \cong -4.0\text{ A}$		14	21	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			3.7		
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		540		pF
Output Capacitance	C_{oss}			131		
Reverse Transfer Capacitance	C_{rss}			105		
Switching^c						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -10\text{ V}$ $R_G = 6\text{ }\Omega$		10	15	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			31	50	
	t_f			20	30	

Notes:

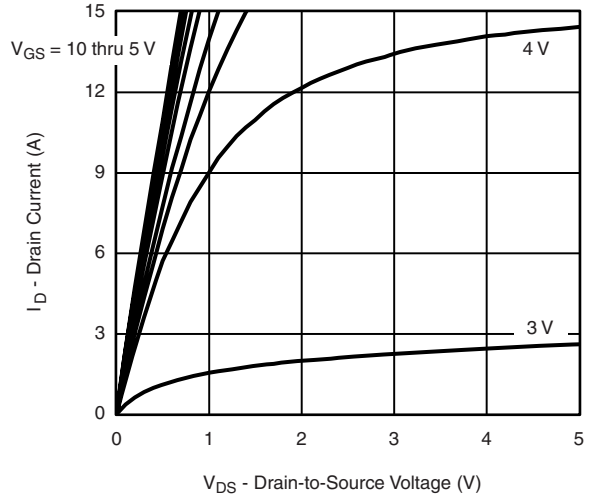
a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. For DESIGN AID ONLY, not subject to production testing.

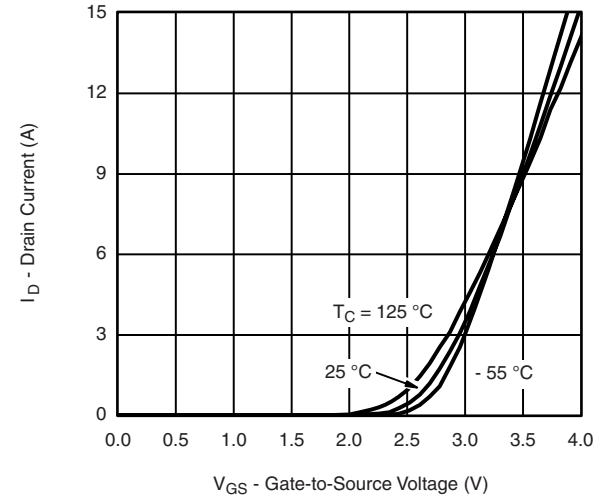
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

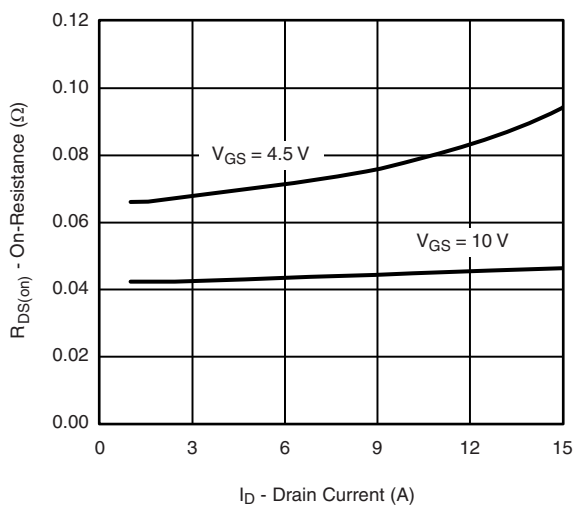
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



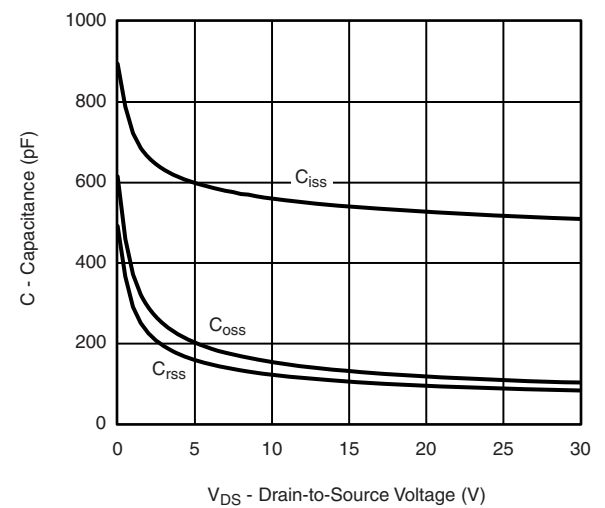
Output Characteristics



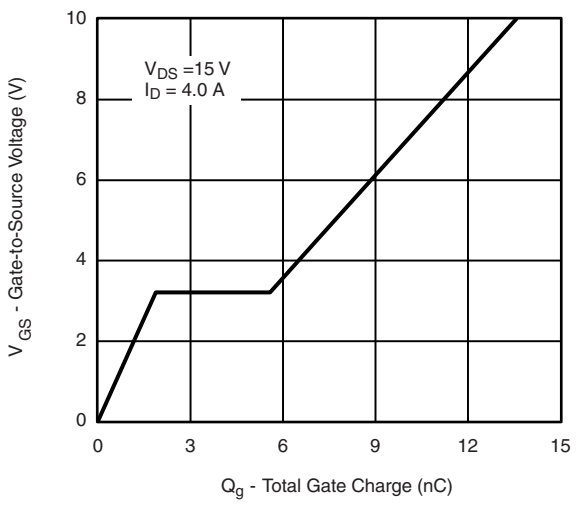
Transfer Characteristics



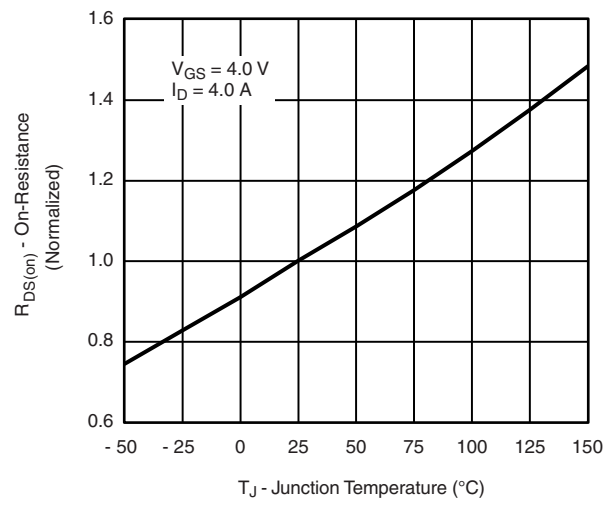
On-Resistance vs. Drain Current



Capacitance

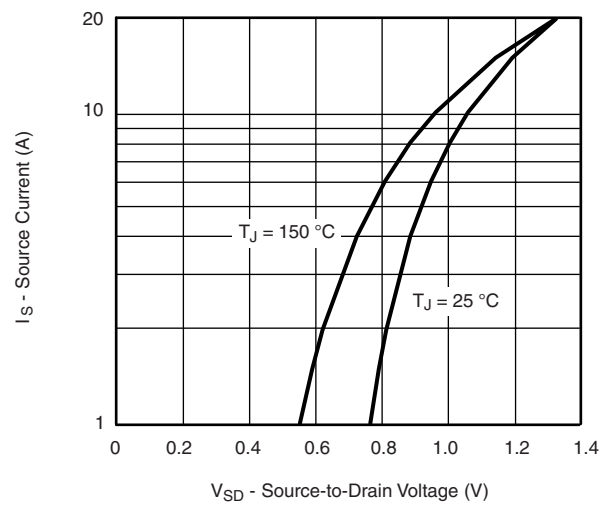


Gate Charge

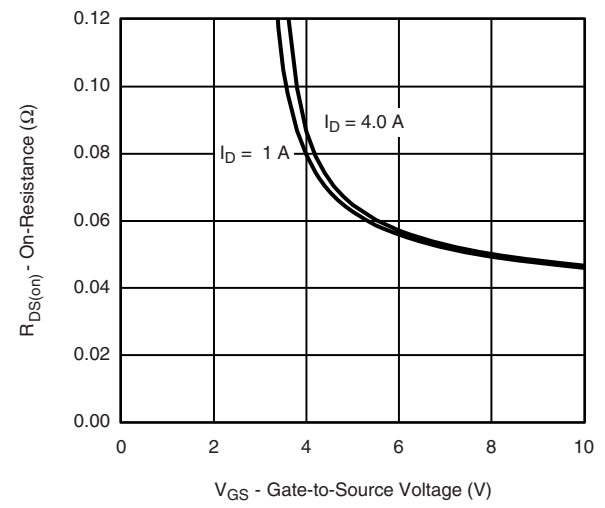


On-Resistance vs. Junction Temperature

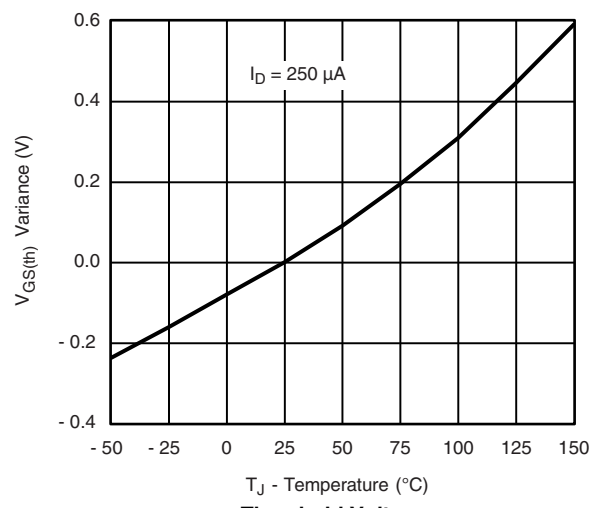
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



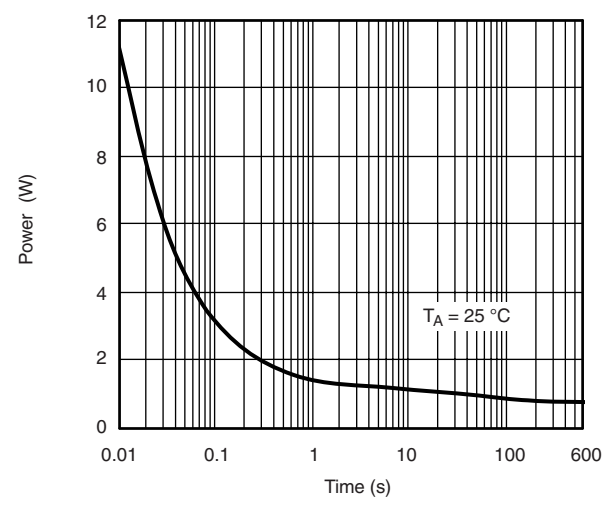
Source-Drain Diode Forward Voltage



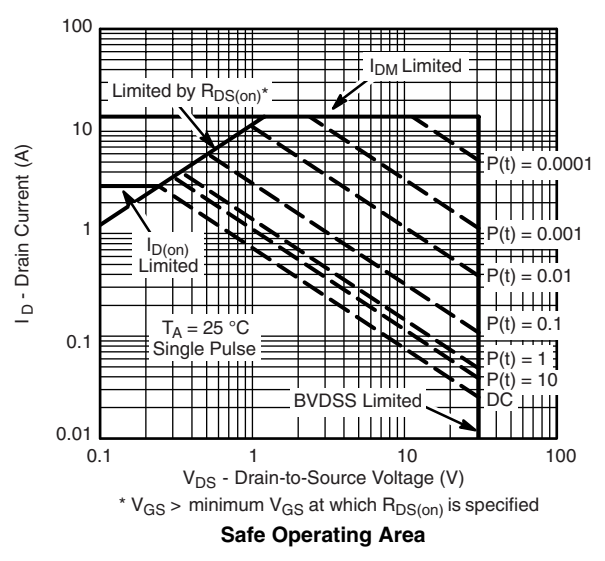
On-Resistance vs. Gate-to-Source Voltage



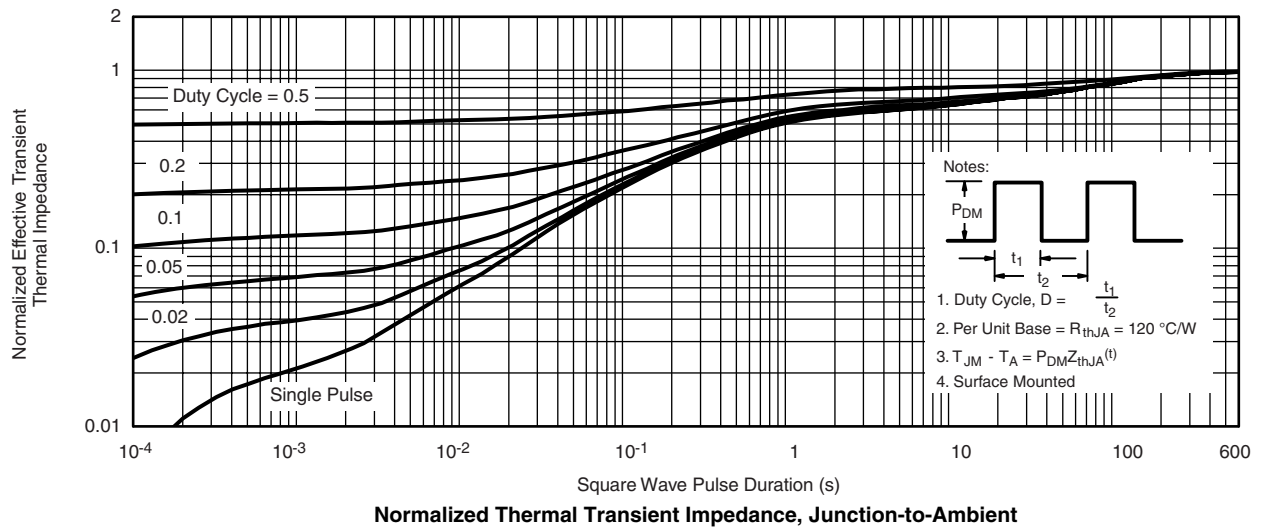
Threshold Voltage



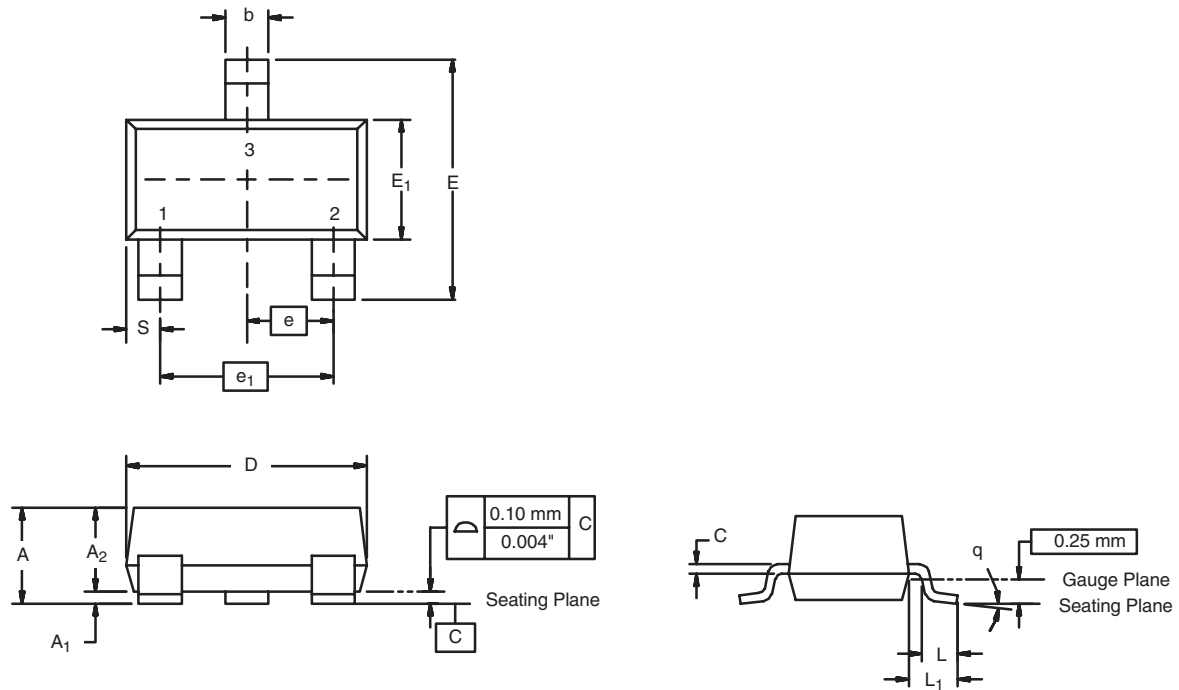
Single Pulse Power



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



SOT-23



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
DWG: 5479

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